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Search Results -

Terms	Documents
(silicon adj nitride) same (C4F6 or C5F8) same etch$	1

Database: US Patents Full-Text Database; US Pre-Grant Publication Full-Text Database; JPO Abstracts Database; EPO Abstracts Database; Derwent World Patents Index; IBM Technical Disclosure Bulletins

Search: L3

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Search History

DATE: Friday, May 24, 2002 Printable Copy Create Case

Set Name side by side	Query	Hit Count	Set Name result set
DB=USPT; PLUR=YES; OP=ADJ			
L1	(silicon adj nitride) same (C4F6 or C5F8) same etch$	0	L1
DB=DWPI; PLUR=YES; OP=ADJ			
L2	(silicon adj nitride) same (C4F6 or C5F8) same etch$	2	L2
DB=PGPB; PLUR=YES; OP=ADJ			
L3	(silicon adj nitride) same (C4F6 or C5F8) same etch$	1	L3

END OF SEARCH HISTORY

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Search Results - Record(s) 1 through 2 of 2 returned.

☐ 1. Document ID: KR 2001046792 A

L2: Entry 1 of 2 File: DWPI Jun 15, 2001

DERWENT-ACC-NO: 2002-087444
DERWENT-WEEK: 200212

TITLE: Method for forming self-aligned contact hole of semiconductor device

Basic Abstract Text:
DETAILED DESCRIPTION - In the method, after a gate electrode(43) having a polysilicon layer(38), a tungsten silicide(40) and a silicon nitride layer(42) are formed on a semiconductor substrate(30), a spacer(44) is formed from undoped silicate glass(USG) on a sidewall of the gate electrode(43). An interlayer dielectric layer(45) is then formed over the substrate(30) and etched by using an etching gas in which an etch selectivity of the interlayer dielectric layer(45) to the spacer(44) is 15:1 or more. The interlayer dielectric layer(45) is formed from borophospho silicate glass(BPSG) or phospho silicate glass(PSG). The etching gas is preferably composed of C5F8, CH2F2, O2 and Ar, which are mixed with a flow rate of 2:1:2:50.

Basic Abstract Text (2):
DETAILED DESCRIPTION - In the method, after a gate electrode(43) having a polysilicon layer(38), a tungsten silicide(40) and a silicon nitride layer(42) are formed on a semiconductor substrate(30), a spacer(44) is formed from undoped silicate glass(USG) on a sidewall of the gate electrode(43). An interlayer dielectric layer(45) is then formed over the substrate(30) and etched by using an etching gas in which an etch selectivity of the interlayer dielectric layer(45) to the spacer(44) is 15:1 or more. The interlayer dielectric layer(45) is formed from borophospho silicate glass(BPSG) or phospho silicate glass(PSG). The etching gas is preferably composed of C5F8, CH2F2, O2 and Ar, which are mixed with a flow rate of 2:1:2:50.

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | Claims | KWIC | Draw Desc | Image

☐ 2. Document ID: JP 2000349071 A

L2: Entry 2 of 2 File: DWPI Dec 15, 2000

DERWENT-ACC-NO: 2001-185436
DERWENT-WEEK: 200119

TITLE: Chemical dry etching procedure for semiconductor device, involves etching film by activation of mixed gas on semiconductor substrate

Basic Abstract Text:

NOVELTY - The method involves etching the film by activation of mixed gas containing oxygen, nitrogen and octafluoro cyclopentene (C5F8) on the semiconductor substrate (9) in the etching chamber (5). The film that is etched is a photoresist film, polysilicon film or silicon nitride film.

Basic Abstract Text (1):
NOVELTY - The method involves etching the film by activation of mixed gas containing oxygen, nitrogen and octafluoro cyclopentene (C5F8) on the semiconductor substrate (9) in the etching chamber (5). The film that is etched is a photoresist film, polysilicon film or silicon nitride film.

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Terms	Documents
(silicon adj nitride) same (C4F6 or C5F8) same etch$	2

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Search Results - Record(s) 1 through 1 of 1 returned.

☐ 1. Document ID: US 20020039843 A1

L3: Entry 1 of 1 File: PGPB Apr 4, 2002

PGPUB-DOCUMENT-NUMBER: 20020039843
PGPUB-FILING-TYPE: new
DOCUMENT-IDENTIFIER: US 20020039843 A1

TITLE: Method of manufacturing a semiconductor integrated circuit device

PUBLICATION-DATE: April 4, 2002

INVENTOR-INFORMATION:

NAME	CITY	STATE	COUNTRY	RULE-47
Ikeda, Takenobu	Ome		JP	
Tadokoro, Masahiro	Hachioji		JP	
Izawa, Masaru	Hino		JP	
Yunogami, Takashi	Sagamihara		JP	

US-CL-CURRENT: 438/738

Full | Title | Citation | Front | Review | Classification | Date | Reference | Sequences | Attachments | KWIC | Draw. Desc | Image

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Terms	Documents
(silicon adj nitride) same (C4F6 or C5F8) same etch$	1

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